

## Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ Max	$I_D$ Max $T_c = +25^\circ\text{C}$
30V	21m $\Omega$ @ $V_{GS} = 10\text{V}$	30A
	35m $\Omega$ @ $V_{GS} = 4.5\text{V}$	24A

## Description

This MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

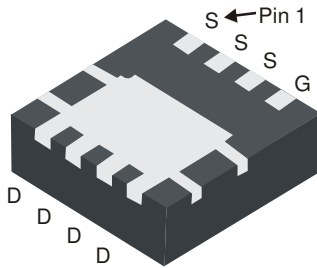
- Backlighting
- Power Management Functions
- DC-DC Converters

## Features and Benefits

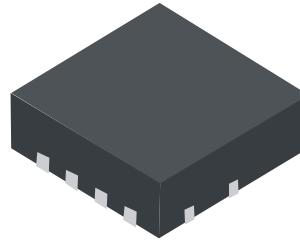
- Low  $R_{DS(ON)}$  – Ensures On-State Losses are Minimized
- Small form factor thermally efficient package enables higher density end products (PowerDI<sup>®</sup>)
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **Qualified to AEC-Q101 standards for High Reliability**
- **An Automotive-Compliant Part is Available Under Separate Datasheet ([DMN3018SFGQ](#))**

## Mechanical Data

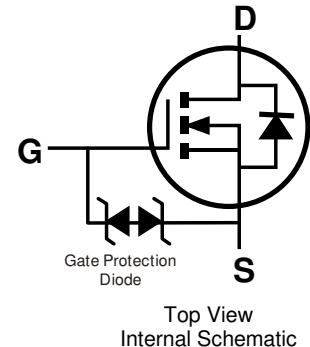
- Case: PowerDI3333-8
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe Solderable per MIL-STD-202, Method 208
- Weight: 0.072 grams (Approximate)



Bottom View



Top View



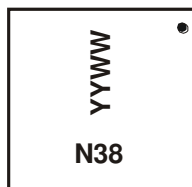
Top View  
Internal Schematic

## Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3018SFG-7	PowerDI3333-8	2000/Tape & Reel
DMN3018SFG-13	PowerDI3333-8	3000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated’s definitions of Halogen- and Antimony-free, “Green” and Lead-free.
  3. Halogen- and Antimony-free “Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



N38 = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Last Digit of Year (ex: 16 = 2016)  
 WW = Week Code (01 – 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		V <sub>DSS</sub>	30	V	
Gate-Source Voltage		V <sub>GSS</sub>	±25	V	
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	Steady State	I <sub>D</sub>	T <sub>C</sub> = +25°C T <sub>C</sub> = +70°C	30 25	A
	Steady State		T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	8.5 6.8	A
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	t < 10s	I <sub>D</sub>	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	11.3 9.1	A
	Steady State		T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	6.6 5.3	A
Continuous Drain Current (Note 6) V <sub>GS</sub> = 4.5V	t < 10s	I <sub>D</sub>	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	8.7 7.0	A
	Steady State		T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	2.5	A
Maximum Continuous Body Diode Forward Current (Note 5)		I <sub>S</sub>	2.5	A	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I <sub>DM</sub>	60	A	
Avalanche Current (Note 7) L = 0.1mH		I <sub>AS</sub>	18	A	
Avalanche Energy (Note 7) L = 0.1mH		E <sub>AS</sub>	16	mJ	

**Thermal Characteristics**

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)		P <sub>D</sub>	1.0	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>θJA</sub>	126	°C/W
	t < 10s		71	
Total Power Dissipation (Note 6)		P <sub>D</sub>	2.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>θJA</sub>	56	°C/W
	t < 10s		31	
Thermal Resistance, Junction to Case (Note 6)		R <sub>θJC</sub>	7.0	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 7)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	µA	V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±10	µA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b> (Note 7)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	1.7	2.1	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	16	21	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 10A
		—	21	35		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 8.5A
Diode Forward Voltage	V <sub>SD</sub>	0.5	—	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1A
<b>DYNAMIC CHARACTERISTICS</b> (Note 8)						
Input Capacitance	C <sub>ISS</sub>	—	697	—	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>OSS</sub>	—	97	—	pF	
Reverse Transfer Capacitance	C <sub>RSS</sub>	—	67	—	pF	
Gate resistance	R <sub>G</sub>	—	1.47	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>G</sub>	—	6.0	—	nC	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 15V, I <sub>D</sub> = 9A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>G</sub>	—	13.2	—	nC	
Gate-Source Charge	Q <sub>GS</sub>	—	2.2	—	nC	
Gate-Drain Charge	Q <sub>GD</sub>	—	1.8	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	4.3	—	ns	V <sub>DD</sub> = 15V, V <sub>GS</sub> = 10V, R <sub>L</sub> = 15Ω, I <sub>D</sub> = 1A, R <sub>G</sub> = 6Ω
Turn-On Rise Time	t <sub>R</sub>	—	4.4	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	20.1	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	4.1	—	ns	
Reverse Recovery Time	T <sub>RR</sub>	—	7.3	—	ns	I <sub>F</sub> = 9A, di/dt = 500A/µs
Reverse Recovery Charge	Q <sub>RR</sub>	—	7.9	—	nC	

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
  - I<sub>AS</sub> and E<sub>AS</sub> rating are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  - Short duration pulse test used to minimize self-heating effect.

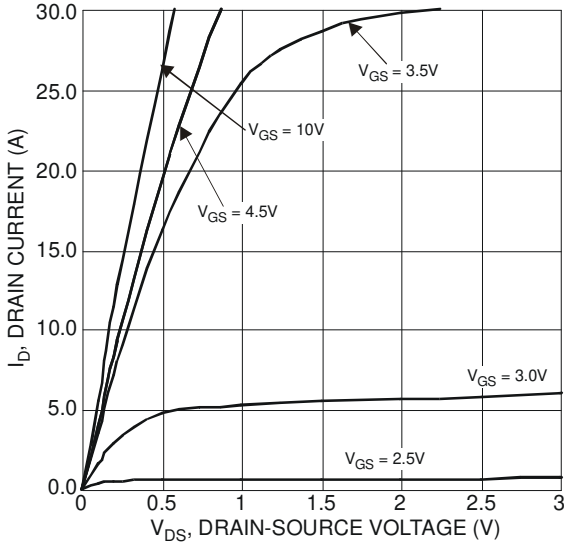


Figure 1 Typical Output Characteristics

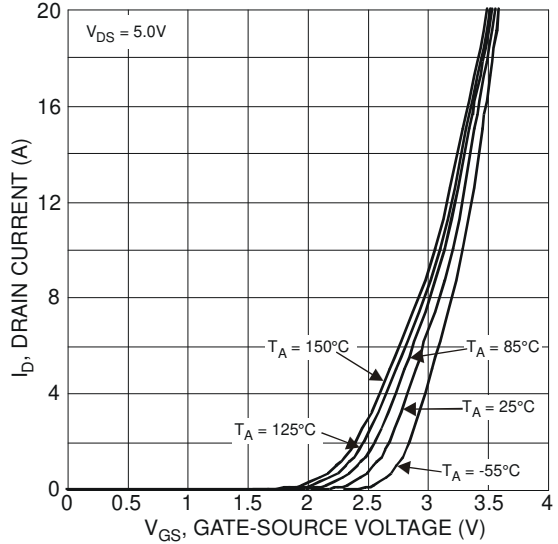


Figure 2 Typical Transfer Characteristics

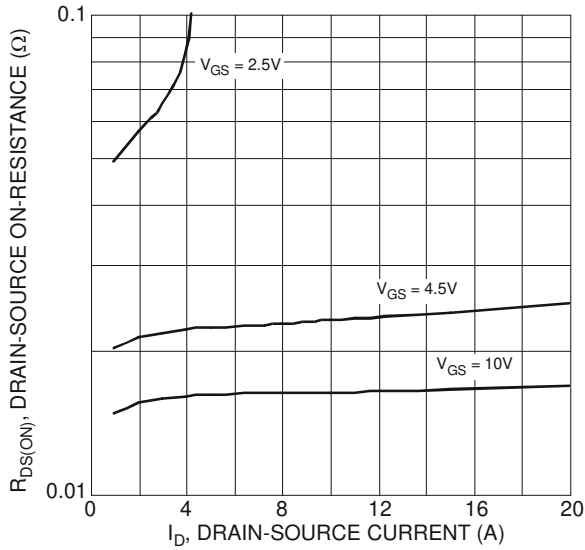


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

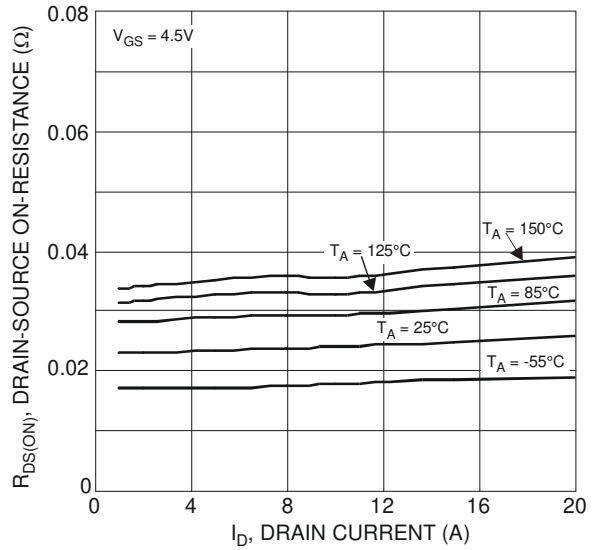


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

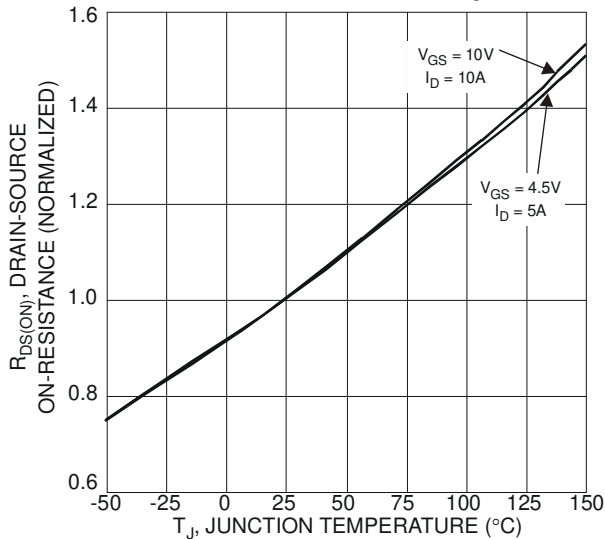


Figure 5 On-Resistance Variation with Temperature

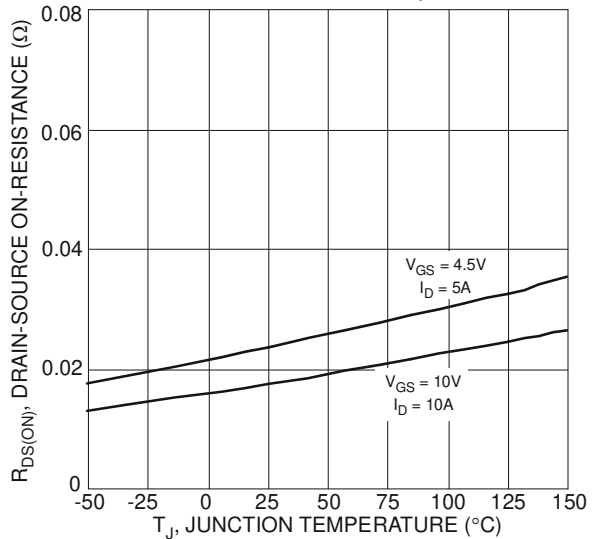


Figure 6 On-Resistance Variation with Temperature

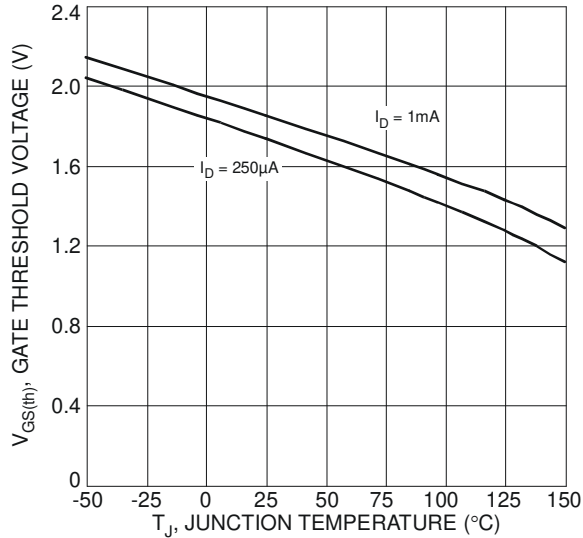


Figure 7 Gate Threshold Variation vs. Ambient Temperature

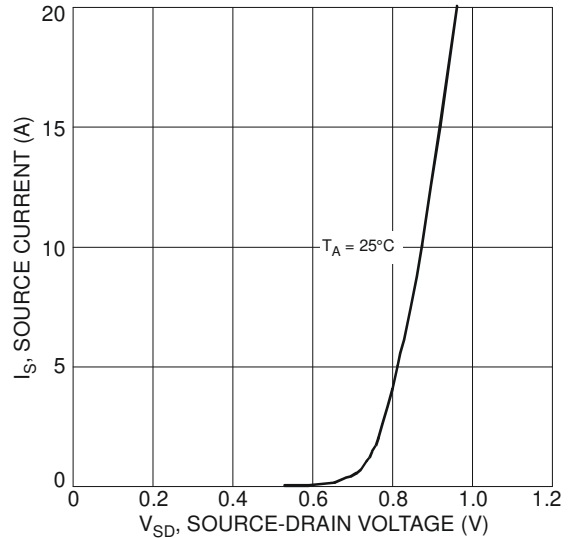


Figure 8 Diode Forward Voltage vs. Current

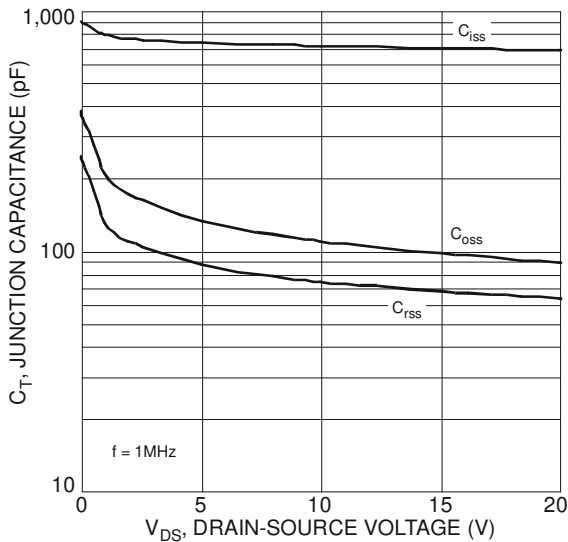


Figure 9 Typical Junction Capacitance

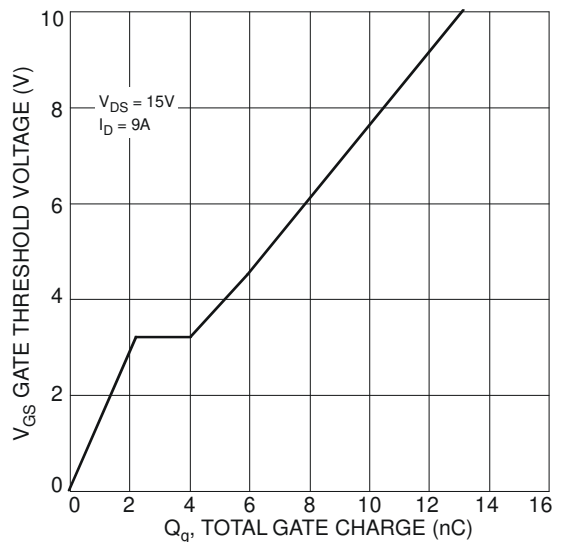


Figure 10 Gate Charge

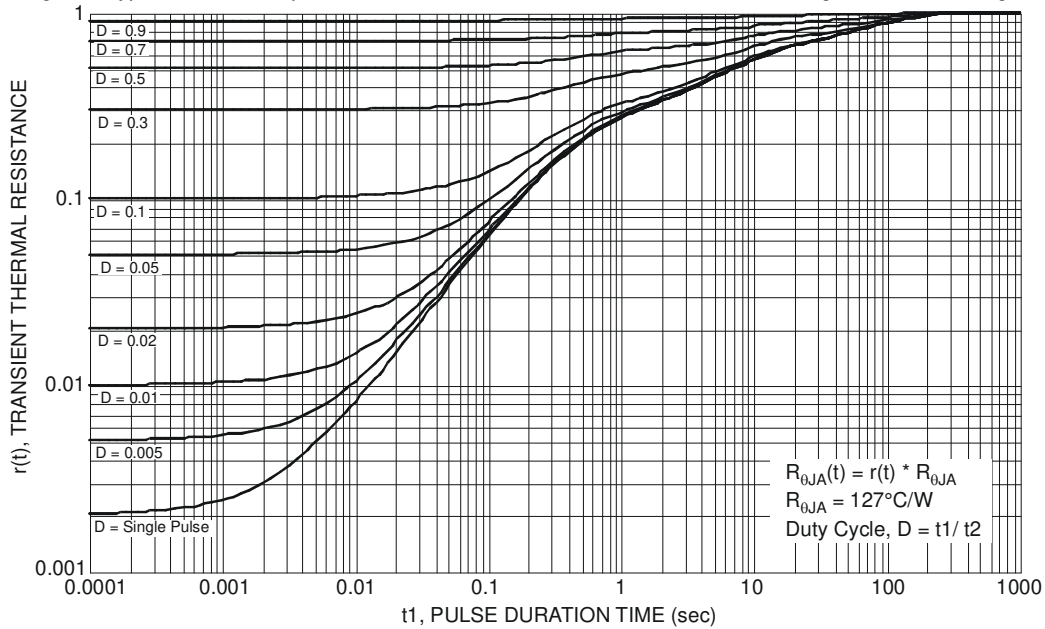


Figure 11 Transient Thermal Resistance

$$R_{\theta JA}(t) = r(t) * R_{\theta JA}$$

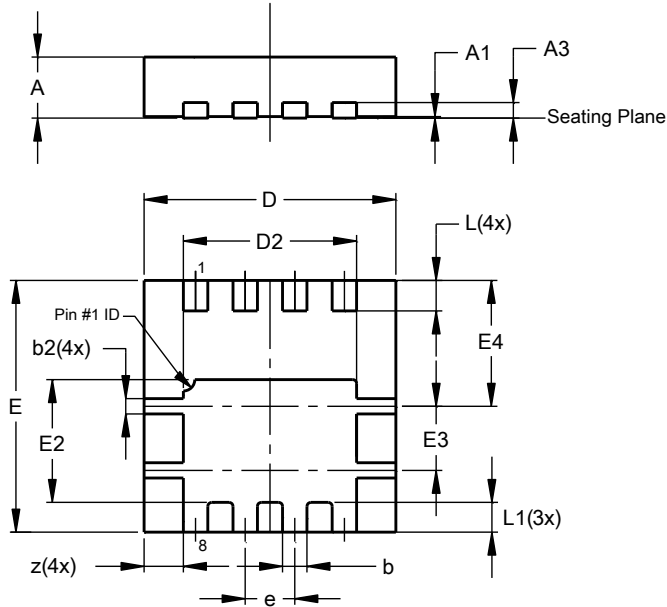
$$R_{\theta JA} = 127^{\circ}\text{C/W}$$

$$\text{Duty Cycle, } D = t1 / t2$$

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI3333-8**

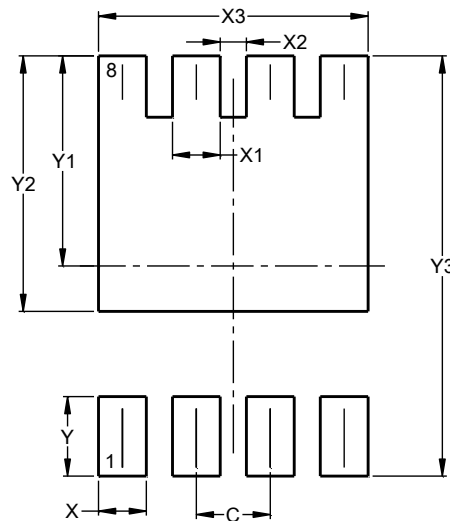


PowerDI3333-8			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	-	-	0.203
b	0.27	0.37	0.32
b2	0.15	0.25	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
E3	0.79	0.89	0.84
E4	1.60	1.70	1.65
e	-	-	0.65
L	0.35	0.45	0.40
L1	-	-	0.39
z	-	-	0.515
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI3333-8**



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700

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